

Amendments to the Specification

Please amend the specification as follows.

Please amend paragraph [0003], at page 1, as follows:

[0003] In a chemical mechanical polishing process, after a surface of a semiconductor substrate has been polished for a certain period of time, the polishing process should be stopped at a desired timing or at the time when the semiconductor substrate has a desired film thickness. For example, some integrated circuit designs require an insulating film (layer) of SiO₂ or the like to be left on a metallic interconnection of copper, aluminum, or the like. Since a metallic layer or other layers are further deposited on the insulating layer in the a subsequent process, such an insulating layer is referred to as an interlayer. In this case, if the semiconductor substrate is excessively polished, then the lower metallic layer is exposed on the polished surface. Therefore, the polishing process needs to be stopped in a state in which a predetermined thickness of the interlayer remains unpolished.